

FIG.1A

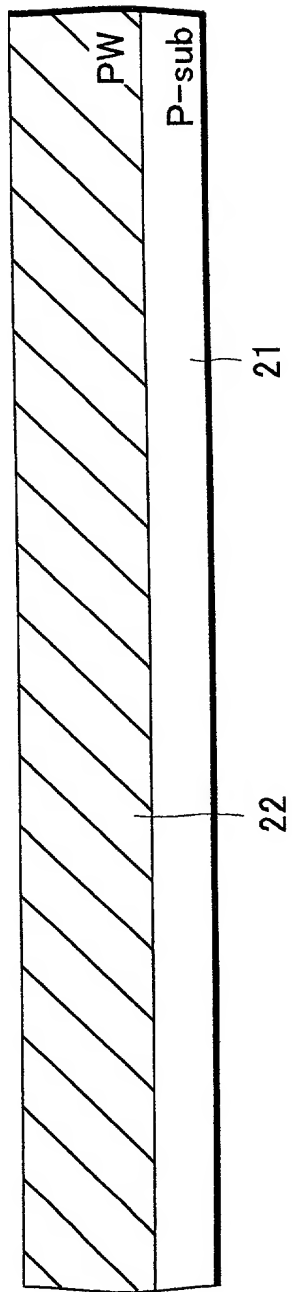


FIG.1B

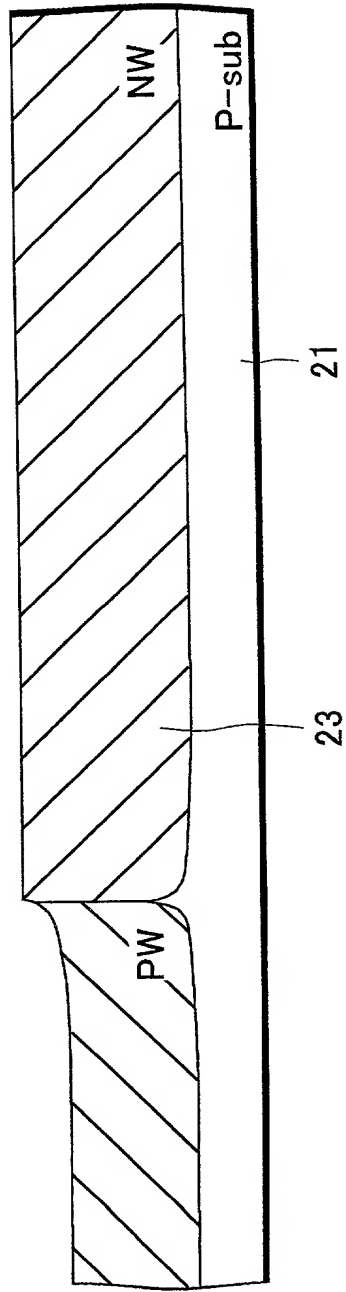


Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate 21 with a P-sub region 22. A series of circular features 24 are arranged along a central axis, with rectangular regions 25 (labeled LN) and 26 (labeled PW) positioned between them. A label PR points to the central axis.

[illegible]



This diagram shows a cross-sectional view of a semiconductor device. A central channel, labeled 21, is formed in a substrate, labeled 22. The channel is defined by a series of gates, labeled 24, which are positioned on the top surface of the channel. The gates are separated by regions labeled 25. The gates are labeled with "N+" and "P" to indicate their doping type. The substrate is labeled "P-sub". The top surface of the device is labeled "PW". The bottom surface of the device is labeled "26". The channel is labeled "21". The gates are labeled "24". The regions between the gates are labeled "25". The substrate is labeled "22". The top surface is labeled "PW". The bottom surface is labeled "26".

This cross-sectional view shows a semiconductor device with a substrate 26 and a p-sub layer 33. A series of gates 22, 23, 27, and 28 are formed on the surface. Contacts 24 are provided for the gates and the substrate. The device includes regions labeled PR, PW, NW, and NW. Doped regions are indicated by N+ and P+ labels. The gates are separated by spacers 30 and 31. The substrate is labeled 26 and the p-sub layer is labeled 33. The gates are labeled 22, 23, 27, and 28. The contacts are labeled 24. The regions are labeled PR, PW, NW, and NW. The doped regions are labeled N+ and P+. The spacers are labeled 30 and 31.

[illegible][illegible]

FIG. 7A

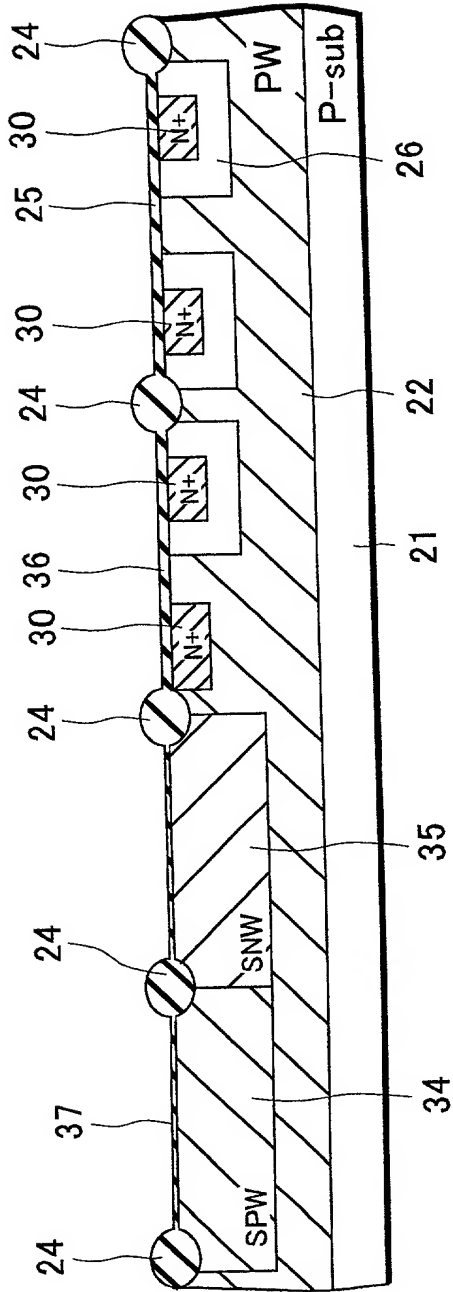


FIG. 7B

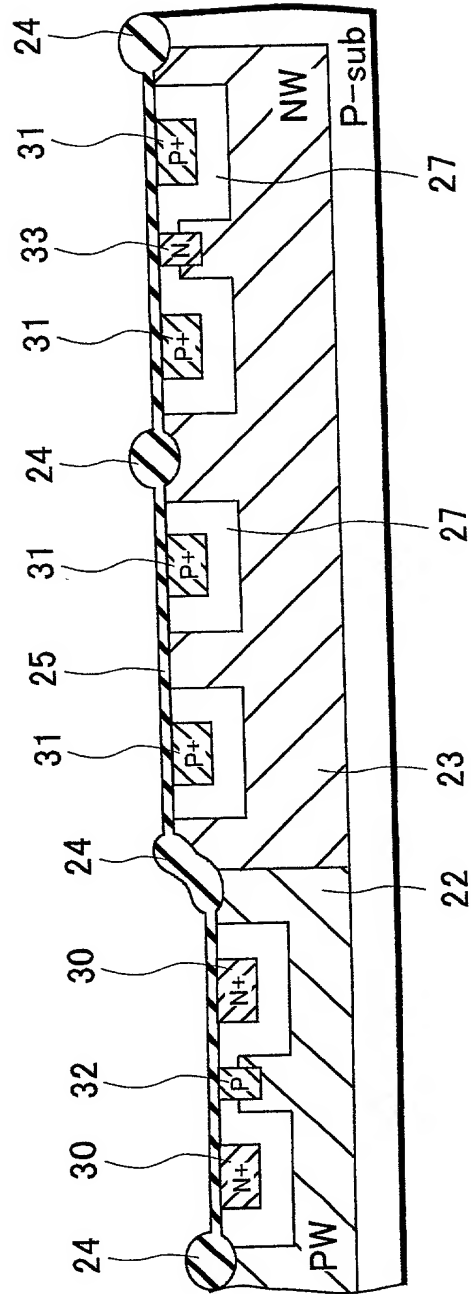






FIG.9A

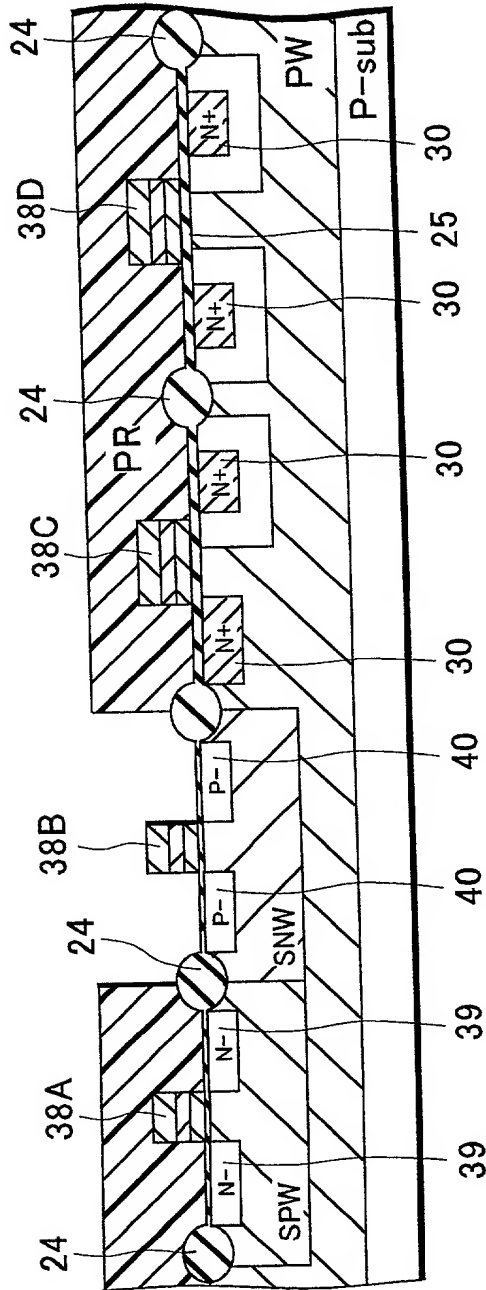
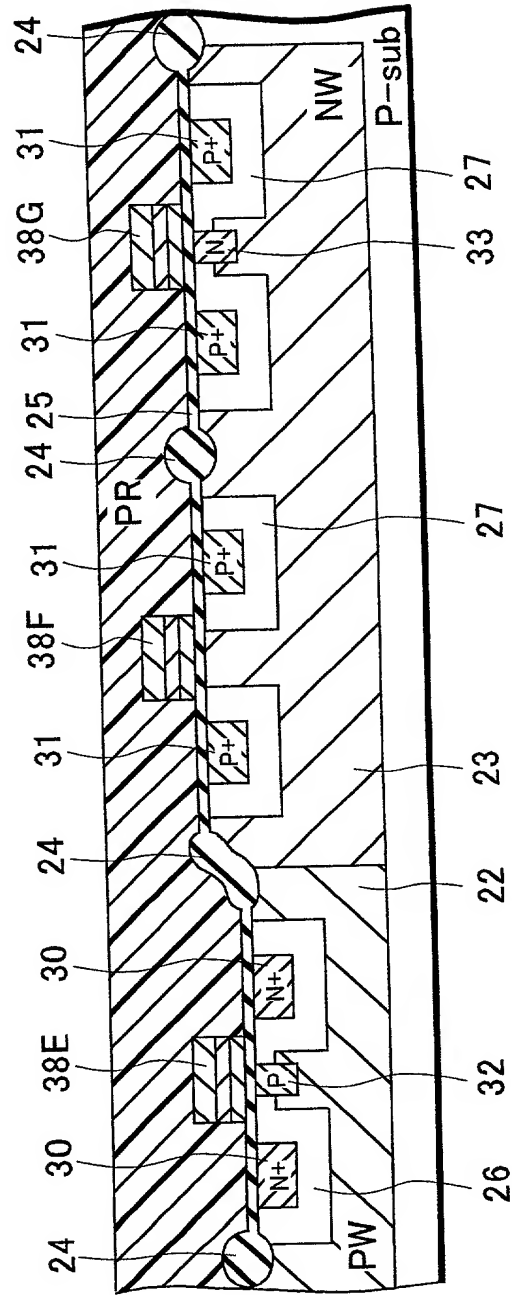


FIG.9B



[illegible]

This cross-sectional view shows a semiconductor device with a substrate 26. A series of gates 22 are formed on the surface, with regions 24, 25, 27, and 30 located between them. Contacts 23 are positioned on top of the gates. The device includes various doped regions: P-wells (PW), N-wells (NW), and P-substrate (P-sub). Specific regions are labeled with 'N+' and 'P+' to indicate their doping type. A region labeled 'PR' is also shown. The device is divided into sections labeled 24, 25, 27, 30, 31, 32, 33, 38E, 38F, 38G, and 41.

FIG. 11A

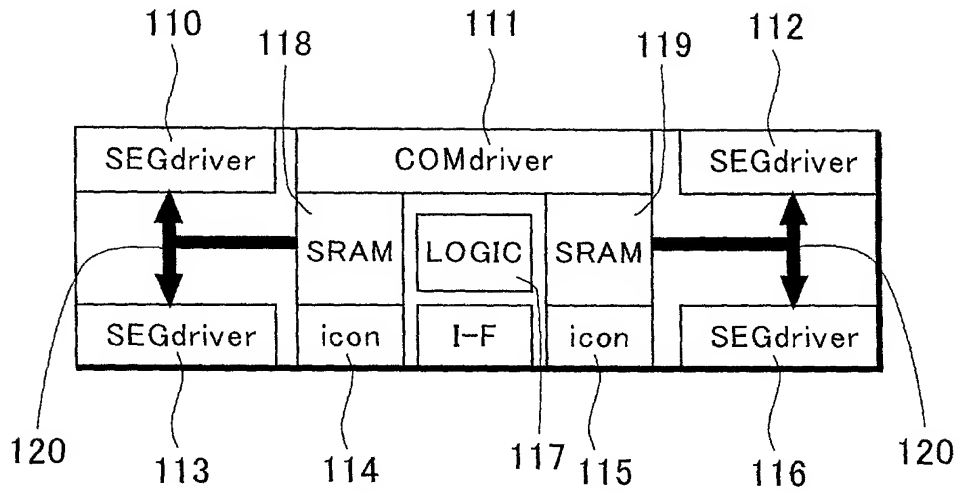


FIG. 11B

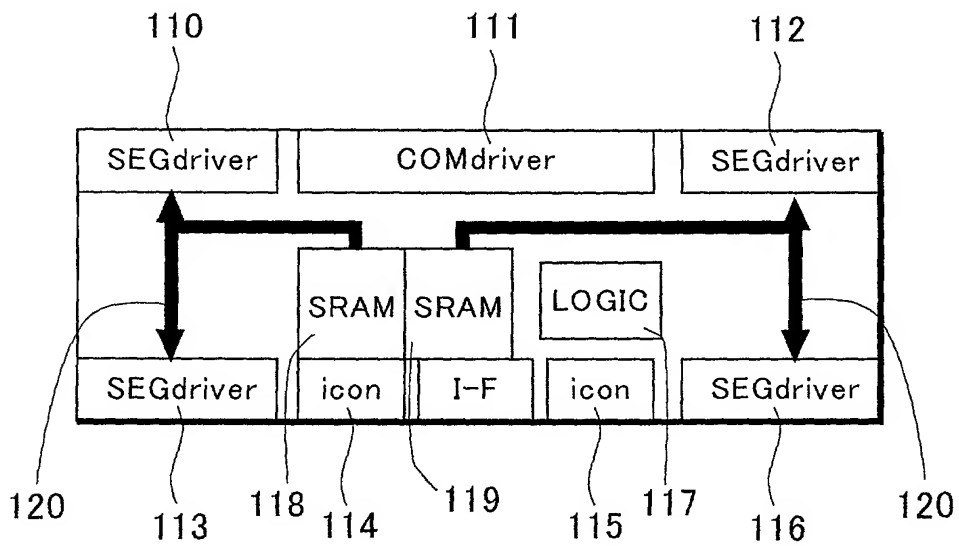


FIG. 12

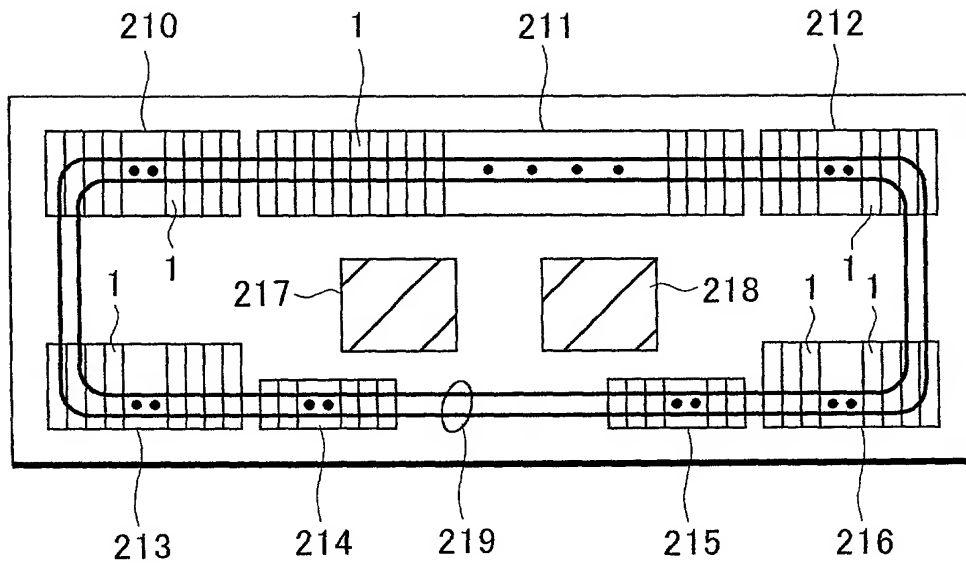


FIG. 13

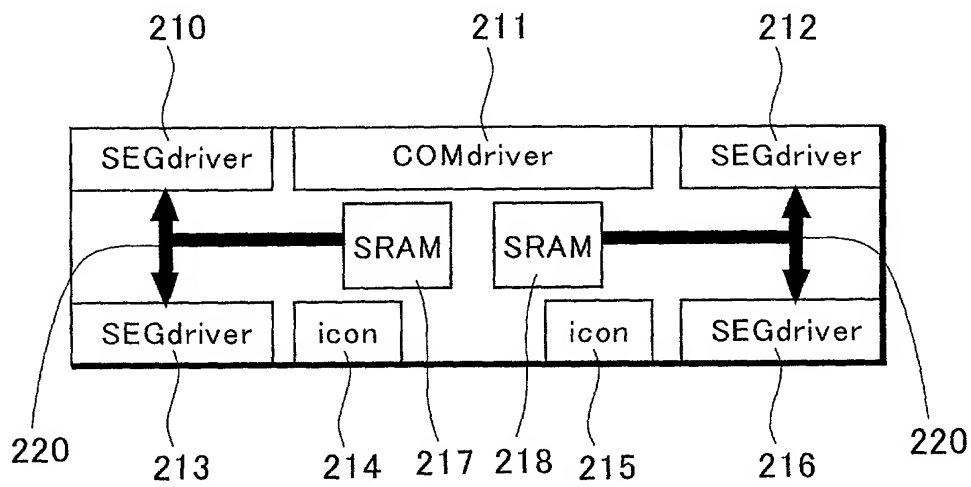


FIG.14A

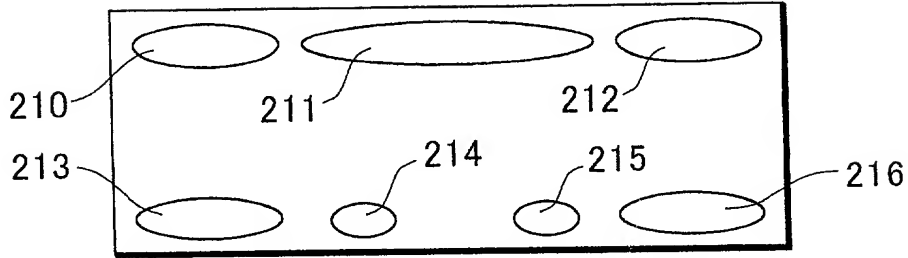


FIG.14B

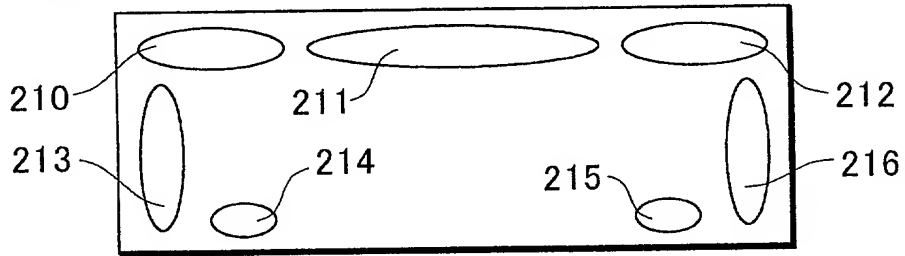


FIG.14C

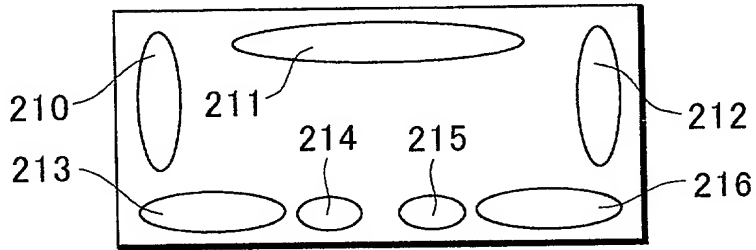


FIG.14D

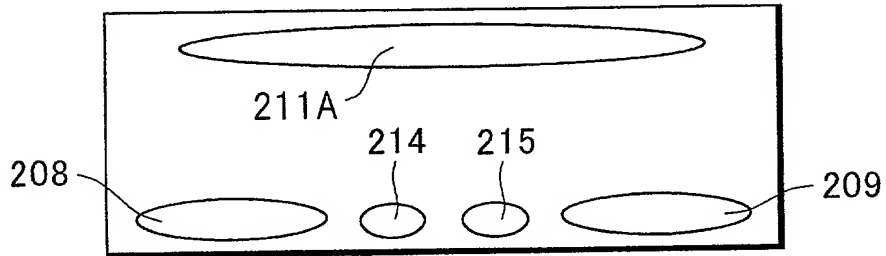


FIG. 15

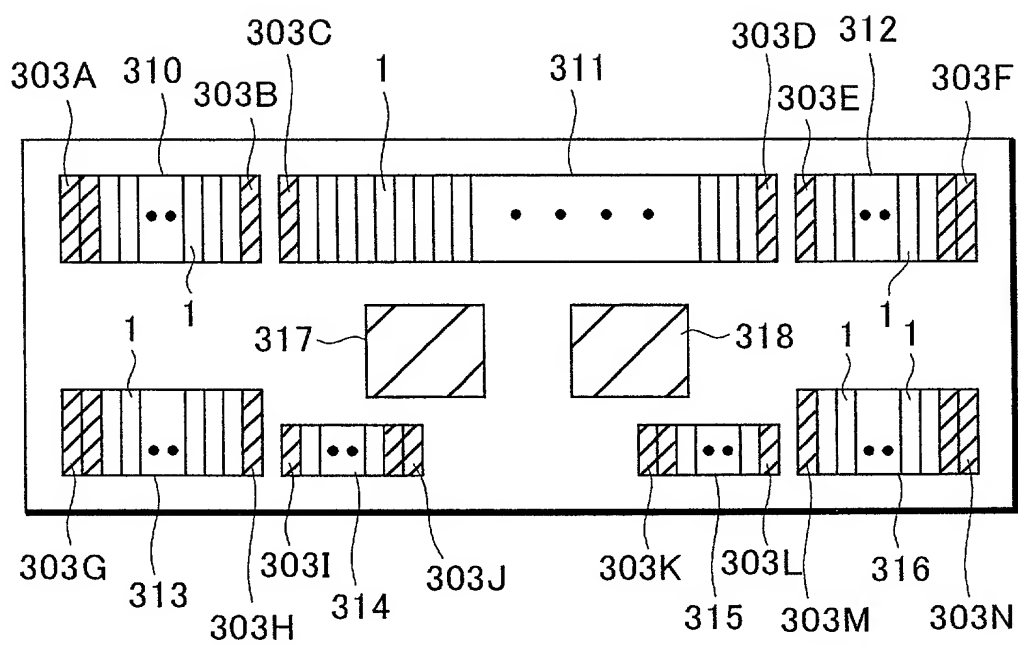


FIG. 16

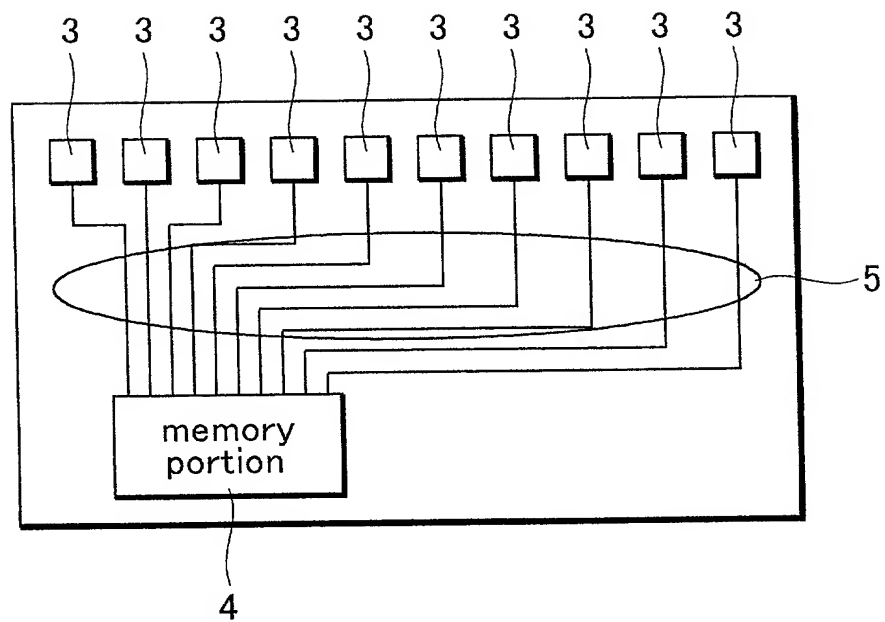


FIG.17A

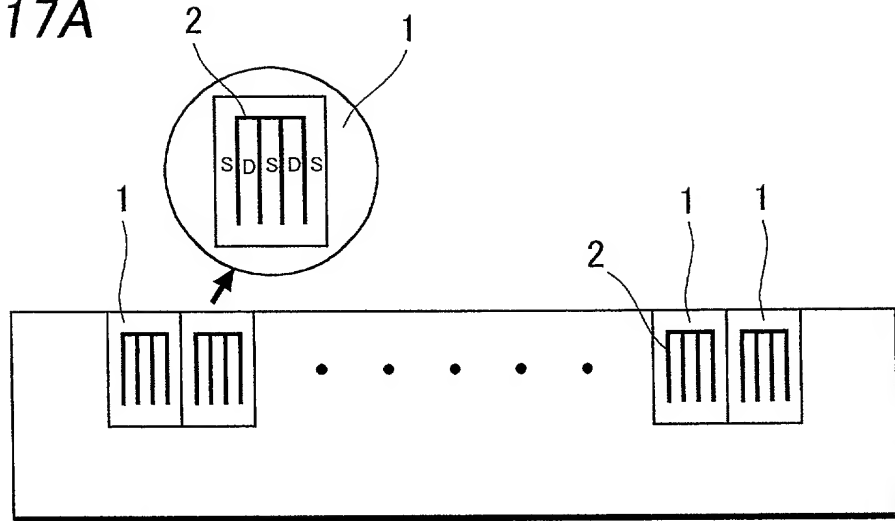


FIG.17B

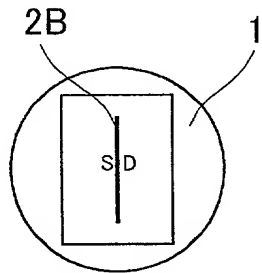


FIG.17C

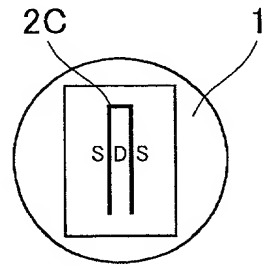


FIG.17D

